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Advanced Power MOSFET

FEATURES

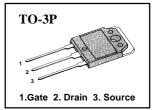
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175°C Operating Temperature
- Lower Leakage Current : 10 μ A (Max.) @ V_{DS} = 100V
- Lower $R_{DS(ON)}$: 0.018 Ω (Typ.)

SSH70N10A

 $BV_{DSS} = 100 V$

 $\mathsf{R}_{\mathsf{DS(on)}} = \ 0.023\,\Omega$

 $I_{\rm D} = 70 \, {\rm A}$



Absolute Maximum Ratings

Symbol	Symbol Characteristic		Value	Units	
V _{DSS}	Drain-to-Source Voltage		100	V	
I	Continuous Drain Current (T _C =25 °C)		70		
Ι _D	I _D Continuous Drain Current (T _c =100 °C)		49.2	— A	
I _{DM}	Drain Current-Pulsed	0	280	А	
V _{GS}	Gate-to-Source Voltage		± 20	V	
E _{AS}	Single Pulsed Avalanche Energy	0	1633	mJ	
I _{AR}	Avalanche Current	0	70	Α	
E _{AR}	Repetitive Avalanche Energy	0	30	mJ	
dv/dt	Peak Diode Recovery dv/dt	0	6.5	V/ns	
Р	Total Power Dissipation (T _c =25 °c)		300	W	
P _D	Linear Derating Factor		2.0	W/°C	
т т	Operating Junction and				
T_J , T_STG	Storage Temperature Range		- 55 to +175		
Ŧ	Maximum Lead Temp. for Soldering		200	°C	
TL	Purposes, 1/8" from case for 5-second	s	300		

Thermal Resistance

Symbol	Characteristic	Тур.	Max.	Units
R _{tuc}	Junction-to-Case		0.5	
R _{0CS}	Case-to-Sink	0.24		°C /W
R _{θJA}	Junction-to-Ambient		40	



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SSH70N10A

N-CHANNEL POWER MOSFET

Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition	
BV _{DSS}	Drain-Source Breakdown Voltage	100			V	V _{GS} =0V,I _D =250	
$\Delta BV/\Delta T_{J}$	Breakdown Voltage Temp. Coeff.		0.12		V/ ℃	I _D =250μA See Fig 7	
V _{GS(th)}	Gate Threshold Voltage	2.0		4.0	V	V _{DS} =5V,I _D =250μA	
I _{GSS}	Gate-Source Leakage, Forward			100	nA	V _{GS} =20V	
GSS	Gate-Source Leakage, Reverse			-100		V _{GS} =-20V	
	Droin to Source Leokage Current			10		V _{DS} =100V	
I _{DSS}	Drain-to-Source Leakage Current			100	μA	V _{DS} =80V,T _C =150°C	
R _{DS(on)}	Static Drain-Source On-State Resistance			0.023	Ω	V _{GS} =10V,I _D =35A ④	
9 _{fs}	Forward Transconductance		53.51		Ω	V _{DS} =40V,I _D =35A ④	
C _{iss}	Input Capacitance		3750	4870		(1 - 0)/(1) - 25)/(f - 1)/(1-25)/(f - 1)/(f -	
C _{oss}	Output Capacitance		850	980	pF	V _{GS} =0V,V _{DS} =25V,f =1MHz See Fig 5	
C _{rss}	Reverse Transfer Capacitance		375	430		See Fig 5	
t _{d(on)}	Turn-On Delay Time		22	60		V _{DD} =50V,I _D =70A,	
t _r	Rise Time		24	60	-	$R_{G}=5.3\Omega$	
t _{d(off)}	Turn-Off Delay Time		112	240	ns	See Fig 13 @5	
t _f	Fall Time		84	180			
Q _g	Total Gate Charge		151	195		V _{DS} =80V,V _{GS} =10V,	
Q _{gs}	Gate-Source Charge		31		nC	I _D =70A	
Q _{gd}	Gate-Drain("miller") Charge		66			See Fig 6 & Fig 12 46	

Electrical Characteristics ($T_C=25$ °C unless otherwise specified)

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Тур.	Max.	Units	Test Condition
ا _s	Continuous Source Current			70	^	Integral reverse pn-diode
I _{SM}	Pulsed-Source Current			280	А	in the MOSFET
V _{SD}	Diode Forward Voltage			1.6	V	T _J =25°C,I _S =70A,V _{GS} =0V
t _{rr}	Reverse Recovery Time		143		ns	T _J =25°C,I _F =70A
Q _{rr}	Reverse Recovery Charge		0.72		μC	$di_F/dt=100A/\mu s$

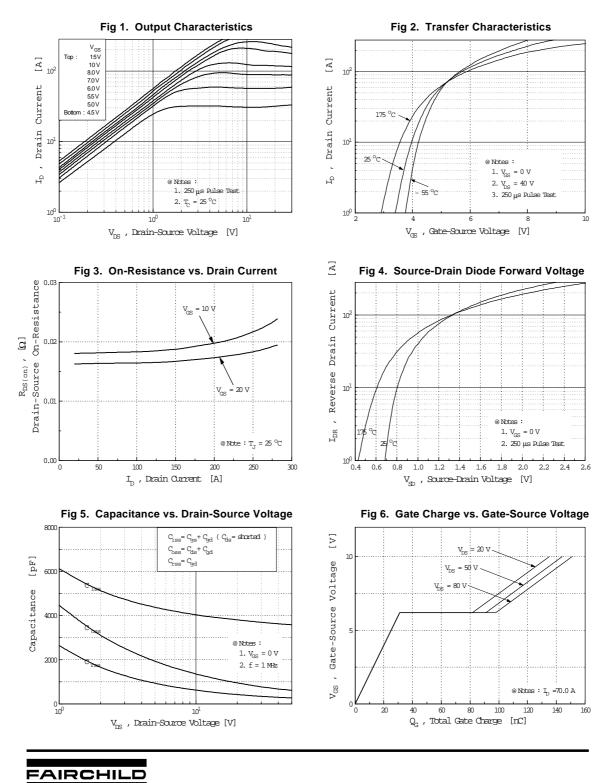
Notes;

- () Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- 2 L=0.5mH, I_{AS} =70A, V_{DD} =25V, R_{G} =27 Ω , Starting T_{J} =25°C
- $\begin{array}{ll} \hline & I_{\text{SD}} \leq 70\text{A}, \text{ di/dt} \leq 530\text{A/}\mu\text{s}, V_{\text{DD}} \leq \text{BV}_{\text{DSS}}, \text{ Starting } \text{T}_{\text{J}} = 25^{\circ}\text{C} \\ \hline & \text{Pulse Test}: \text{Pulse Width} = 250 \ \mu\text{s}, \text{Duty Cycle} \quad \leq 2\% \end{array}$
- 5 Essentially Independent of Operating Temperature

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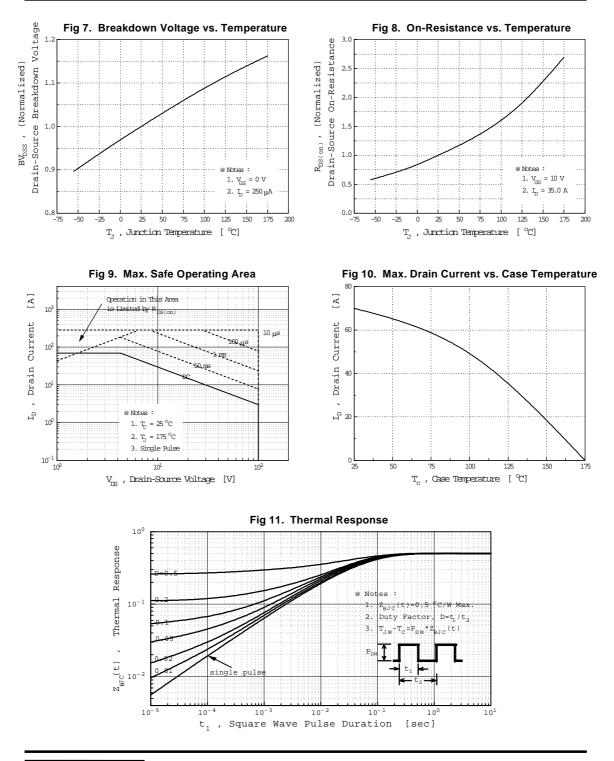
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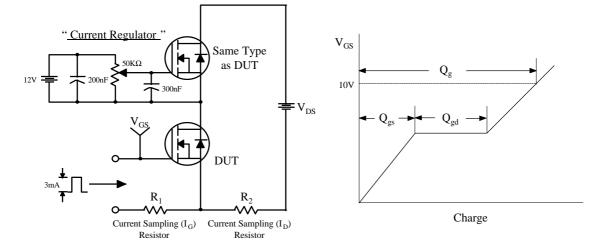


Fig 12. Gate Charge Test Circuit & Waveform



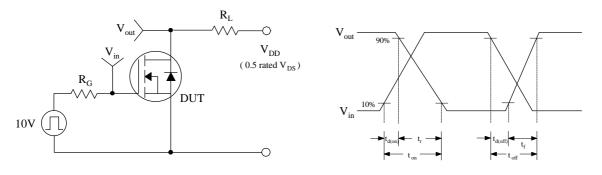
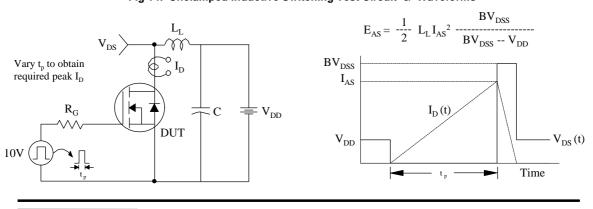
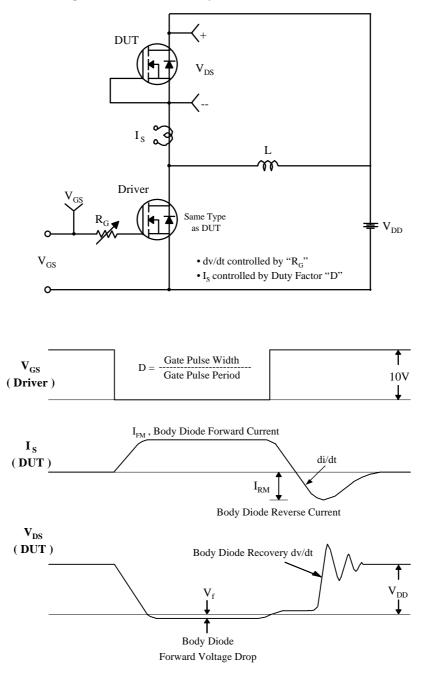
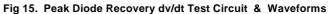


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms











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